

MOSFETs Silicon N-Channel MOS (DTMOSIV)

TK16N60W

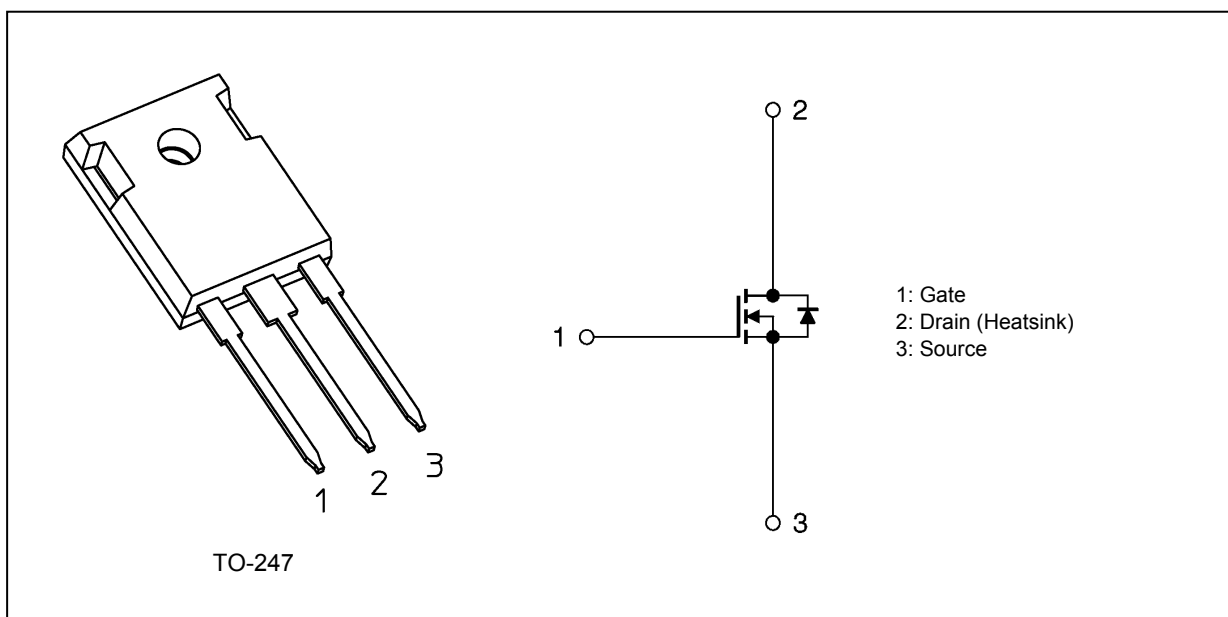
1. Applications

- Switching Voltage Regulators

2. Features

- (1) Low drain-source on-resistance: $R_{DS(ON)} = 0.16 \Omega$ (typ.)
by used to Super Junction Structure : DTMOS
- (2) Easy to control Gate switching
- (3) Enhancement mode: $V_{th} = 2.7$ to 3.7 V ($V_{DS} = 10$ V, $I_D = 0.79$ mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) ($T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	V_{DSS}	600	V
Gate-source voltage	V_{GSS}	± 30	
Drain current (DC) (Note 1)	I_D	15.8	A
Drain current (pulsed) (Note 1)	I_{DP}	63.2	
Power dissipation ($T_c = 25^\circ\text{C}$)	P_D	130	W
Single-pulse avalanche energy (Note 2)	E_{AS}	231	mJ
Avalanche current	I_{AR}	4.0	A
Reverse drain current (DC) (Note 1)	I_{DR}	15.8	
Reverse drain current (pulsed) (Note 1)	I_{DRP}	63.2	
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to 150	
Mounting torque	TOR	0.8	N · m

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	$R_{th(ch-c)}$	0.962	$^\circ\text{C}/\text{W}$
Channel-to-ambient thermal resistance	$R_{th(ch-a)}$	50	

Note 1: Ensure that the channel temperature does not exceed 150°C .

Note 2: $V_{DD} = 90\text{ V}$, $T_{ch} = 25^\circ\text{C}$ (initial), $L = 25.3\text{ mH}$, $R_G = 25\ \Omega$, $I_{AR} = 4.0\text{ A}$

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

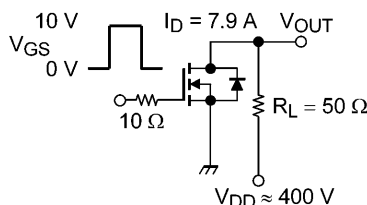
6. Electrical Characteristics

6.1. Static Characteristics ($T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current	I_{GSS}	$V_{GS} = \pm 30\text{ V}, V_{DS} = 0\text{ V}$	—	—	± 1	μA
Drain cut-off current	I_{DSS}	$V_{DS} = 600\text{ V}, V_{GS} = 0\text{ V}$	—	—	10	
Drain-source breakdown voltage	$V_{(BR)DSS}$	$I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$	600	—	—	V
Gate threshold voltage	V_{th}	$V_{DS} = 10\text{ V}, I_D = 0.79\text{ mA}$	2.7	—	3.7	
Drain-source on-resistance	$R_{DS(ON)}$	$V_{GS} = 10\text{ V}, I_D = 7.9\text{ A}$	—	0.16	0.19	Ω

6.2. Dynamic Characteristics ($T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Input capacitance	C_{iss}	$V_{DS} = 300\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	—	1350	—	pF
Reverse transfer capacitance	C_{rss}		—	4	—	
Output capacitance	C_{oss}		—	35	—	
Effective output capacitance	$C_{o(er)}$	$V_{DS} = 0\text{ to }400\text{ V}, V_{GS} = 0\text{ V}$	—	55	—	
Gate resistance	r_g	$V_{DS} = \text{OPEN}, f = 1\text{ MHz}$	—	6	—	Ω
Switching time (rise time)	t_r	See Figure 6.2.1	—	25	—	ns
Switching time (turn-on time)	t_{on}		—	50	—	
Switching time (fall time)	t_f		—	5	—	
Switching time (turn-off time)	t_{off}		—	100	—	
MOSFET dv/dt ruggedness	dv/dt	$V_{DD} = 0\text{ to }400\text{ V}, I_D = 7.9\text{ A}$	50	—	—	V/ns



Duty $\leq 1\%$, $t_w = 10\ \mu\text{s}$

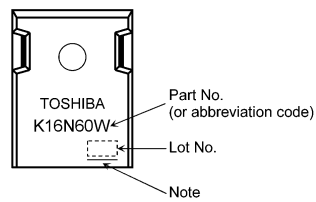
Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics ($T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Q_g	$V_{DD} \approx 400\text{ V}, V_{GS} = 10\text{ V}, I_D = 15.8\text{ A}$	—	38	—	nC
Gate-source charge 1	Q_{gs1}		—	9	—	
Gate-drain charge	Q_{gd}		—	16	—	

6.4. Source-Drain Characteristics ($T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Diode forward voltage	V_{DSF}	$I_{DR} = 15.8\text{ A}, V_{GS} = 0\text{ V}$	—	—	-1.7	V
Reverse recovery time	t_{rr}	$I_{DR} = 7.9\text{ A}, V_{GS} = 0\text{ V}$ $-dI_{DR}/dt = 100\text{ A}/\mu\text{s}$	—	280	—	ns
Reverse recovery charge	Q_{rr}		—	2.9	—	μC
Peak reverse recovery current	I_{rr}		—	23	—	A
Diode dv/dt ruggedness	dv/dt	$I_{DR} = 7.9\text{ A}, V_{GS} = 0\text{ V}, V_{DD} = 400\text{ V}$	15	—	—	V/ns

7. Marking (Note)**Fig. 7.1 Marking**

Note: A line under a Lot No. identifies the indication of product Labels.

Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.

The RoHS is the Directive 2002/95/EC of the European Parliament and of the Council of 27 January 2003 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

8. Characteristics Curves (Note)

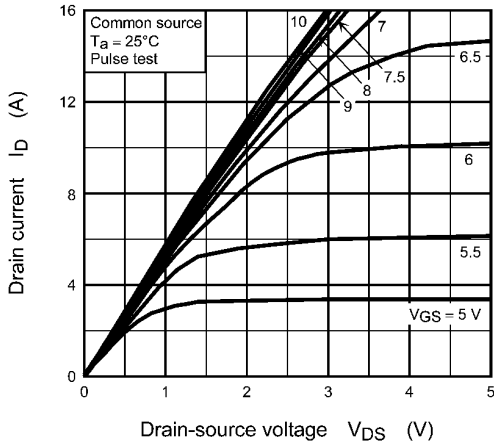


Fig. 8.1 $I_D - V_{DS}$

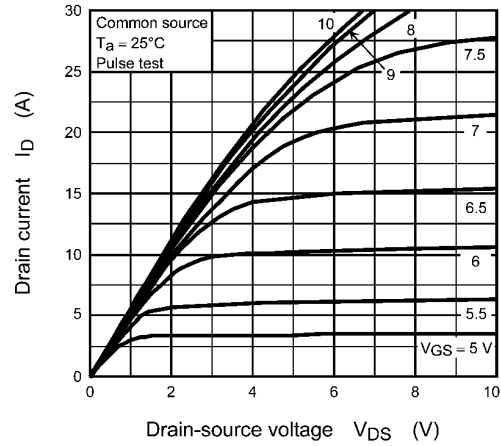


Fig. 8.2 $I_D - V_{DS}$

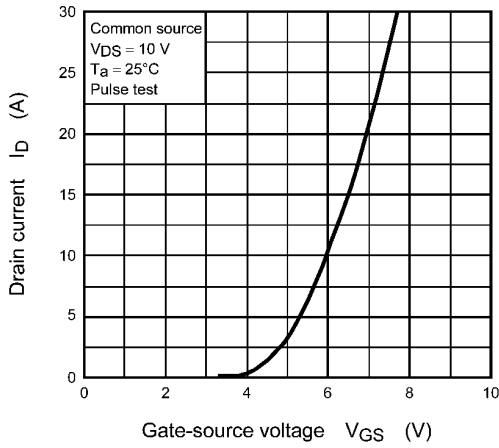


Fig. 8.3 $I_D - V_{GS}$

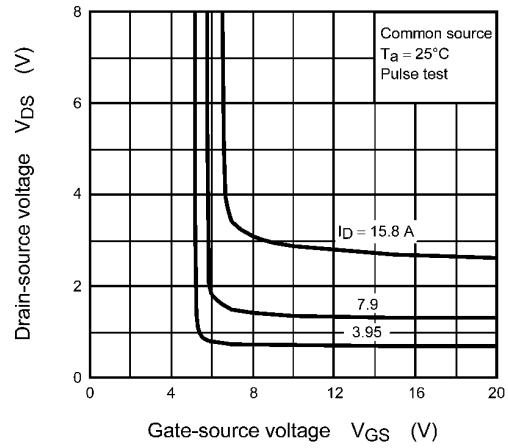


Fig. 8.4 $V_{DS} - V_{GS}$

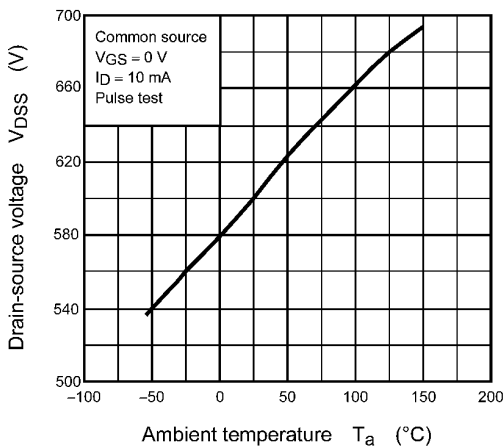


Fig. 8.5 $V_{DSS} - T_a$

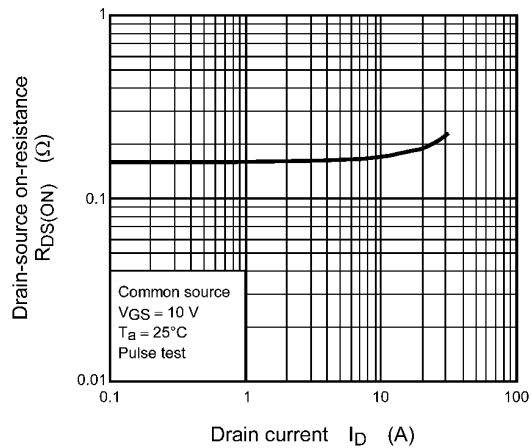


Fig. 8.6 $R_{DS(ON)} - I_D$

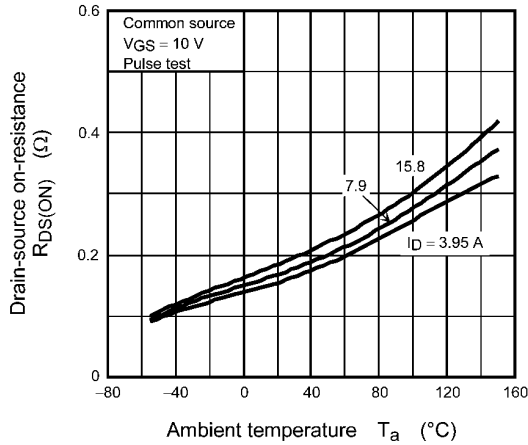


Fig. 8.7 $R_{DS(ON)} - T_a$

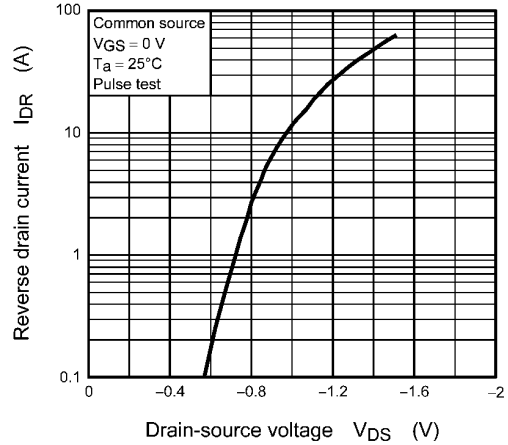


Fig. 8.8 $I_{DR} - V_{DS}$

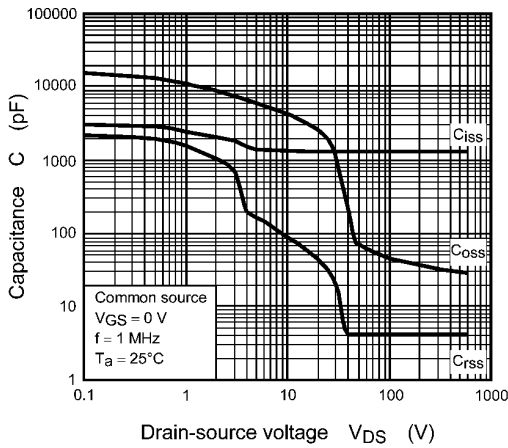


Fig. 8.9 $C - V_{DS}$

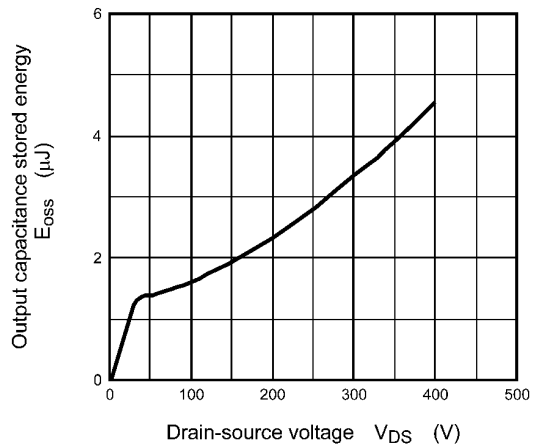


Fig. 8.10 $E_{oss} - V_{DS}$

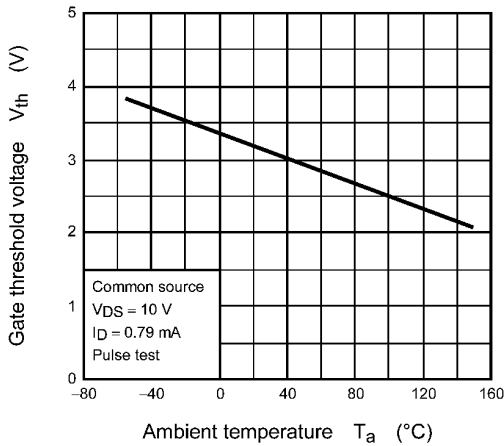


Fig. 8.11 $V_{th} - T_a$

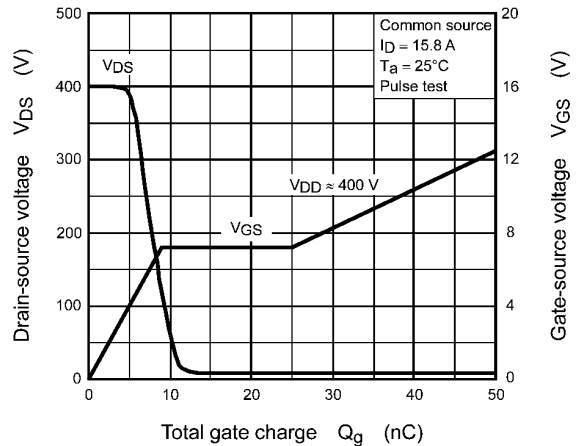


Fig. 8.12 Dynamic Input/Output Characteristics

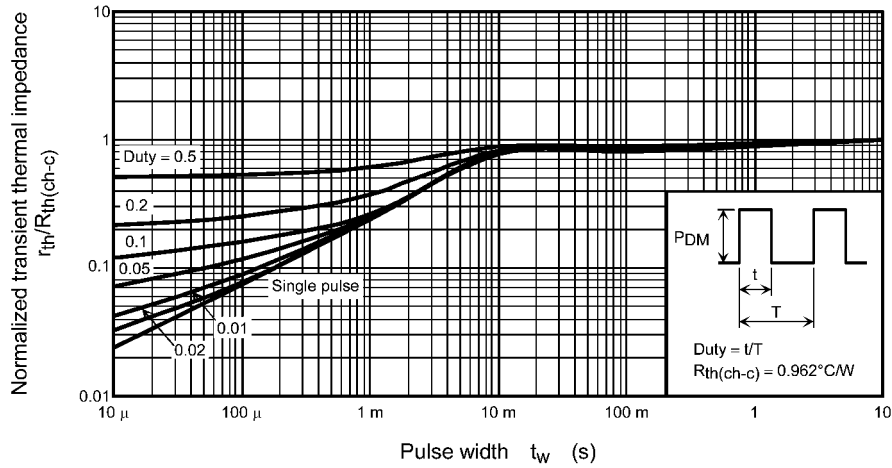


Fig. 8.13 $r_{th} - t_w$
(Guaranteed Maximum)

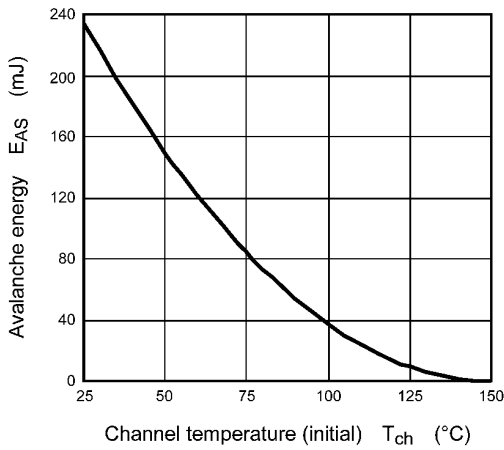


Fig. 8.14 $E_{AS} - T_{ch}$
(Guaranteed Maximum)

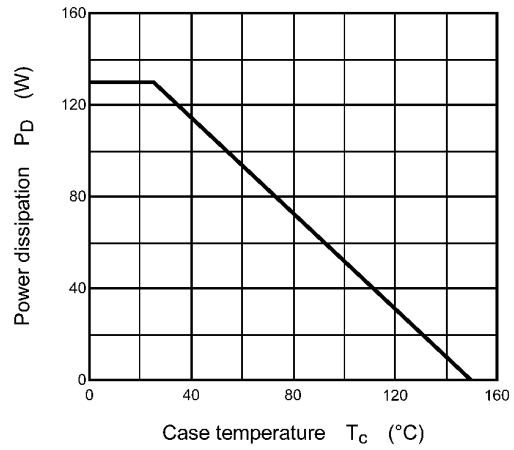
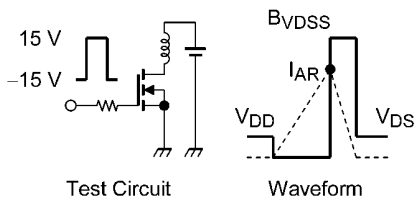


Fig. 8.15 $P_D - T_c$
(Guaranteed Maximum)



$$R_G = 25 \Omega, V_{DD} = 90 \text{ V } E_{AS} = \frac{1}{2} \cdot L \cdot I_{AR}^2 \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$

Fig. 8.16 Test Circuit/Waveform

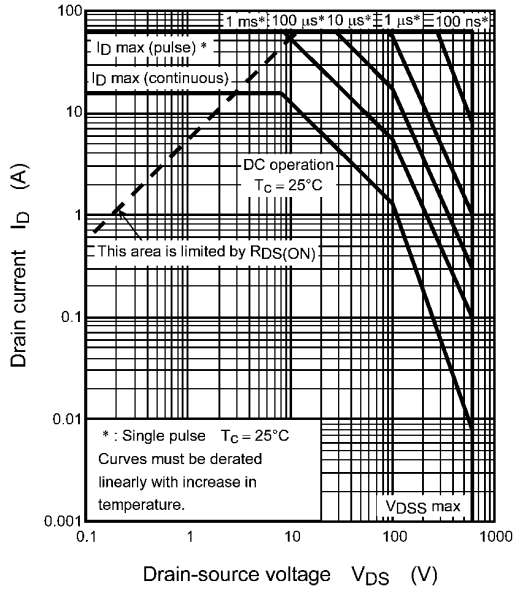


Fig. 8.17 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

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